Asok K Barua

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

141
papers1,556
citations19
h-index32
g-index148
ext. papers1,674
ext. citations2.7
avg, IF3.77
L-index

| # | Paper | IF | Citations |
|-----|--|------------------|-----------|
| 141 | Properties of boron doped ZnO films prepared by reactive sputtering method: Application to amorphous silicon thin film solar cells. <i>Journal of Materials Science and Technology</i> , 2020 , 55, 136-143 | 9.1 | 7 |
| 140 | Mixed-Phase nc-SiOX:H Interlayer to Improve Light Trapping and Shunt Quenching in a-Si:H Solar Cell. <i>IEEE Journal of Photovoltaics</i> , 2019 , 9, 18-25 | 3.7 | 0 |
| 139 | Innovative Utilization of Improved n-doped E-SiOx:H Films to Amplify the Performance of Micromorph Solar Cells. <i>Silicon</i> , 2019 , 11, 487-493 | 2.4 | 3 |
| 138 | Sacrificial layer assisted front textured glass substrate with improved light management in thin film silicon solar cells. <i>Journal of Materials Science: Materials in Electronics</i> , 2019 , 30, 2622-2629 | 2.1 | 1 |
| 137 | Texturization of ZnO:Al surface by reactive ion etching in SF6/Ar, CHF3/Ar plasma for application in thin film silicon solar cells. <i>Journal of Materials Science: Materials in Electronics</i> , 2018 , 29, 6206-6214 | 2.1 | 4 |
| 136 | Parasitic loss mitigation and photocurrent enhancement in amorphous silicon solar cells by using phosphorous-doped fluorinated µc-SiO:H back reflector. <i>Journal of Materials Science: Materials in Electronics</i> , 2018 , 29, 11104-11116 | 2.1 | 2 |
| 135 | Reduction of Hole Injection Barrier Height at TCO/P Interface Using a-SiO:H Interlayer. <i>IEEE Journal of Photovoltaics</i> , 2018 , 8, 8-15 | 3.7 | 3 |
| 134 | Optimization of the texturization of ZnO:Al surface using HCl + HNO3 for application in thin film silicon solar cells. <i>Journal of Materials Science: Materials in Electronics</i> , 2018 , 29, 3210-3218 | 2.1 | 4 |
| 133 | Band Offset Reduction at Defect-Rich p/i Interface Through a Wide Bandgap a-SiO:H Buffer Layer. <i>IEEE Journal of Photovoltaics</i> , 2017 , 7, 414-420 | 3.7 | 12 |
| 132 | Development of Improved n-E-SiO\$_x\$:H Films and Its Innovative Application in Silicon-Based Single Junction Thin Film Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2017 , 7, 892-899 | 3.7 | 4 |
| 131 | Role of dual SiO x: H based buffer at the p/i interface on the performance of single junction microcrystalline solar cells. <i>Materials Science in Semiconductor Processing</i> , 2017 , 66, 9-14 | 4.3 | 1 |
| 130 | Influence of excitation frequency and electrode separation on the growth of microcrystalline silicon films and their application in single junction microcrystalline solar cell. <i>Journal of Materials Science: Materials in Electronics</i> , 2017 , 28, 10382-10390 | 2.1 | 2 |
| 129 | Development of n-type microcrystalline SiOx:H films and its application by innovative way to improve the performance of single junction pc-Si:H solar cell. <i>Journal of Materials Science: Materials in Electronics</i> , 2017 , 28, 5746-5753 | 2.1 | 4 |
| 128 | Blue and violet defect levels mediated absorption hot spots in tapered ZnO nanorods toward improved photocatalytic activity. <i>Journal of Materials Science</i> , 2017 , 52, 12818-12825 | 4.3 | 1 |
| 127 | Effect of oxide based graded buffer and bottom n-layer on the performance of the single junction amorphous silicon solar cells. <i>Journal of Materials Science: Materials in Electronics</i> , 2017 , 28, 16165-161 | 72 ^{.1} | 1 |
| 126 | Numerical modelling on stress and dislocation generation in multi-crystalline silicon during directional solidification for PV applications. <i>Electronic Materials Letters</i> , 2016 , 12, 431-438 | 2.9 | 16 |
| 125 | Hierarchical indium tin oxide (ITO) nano-whiskers: Electron beam deposition and sub-bandgap defect levels mediated visible light driven enhanced photocatalytic activity. <i>Catalysis Communications</i> , 2016 , 87, 86-89 | 3.2 | 7 |

(1993-2015)

| 124 | Fabrication of single junction amorphous silicon solar cell/mini module using novel n-type nanocrystalline SiOx:F:H back reflector. <i>Journal of Materials Science: Materials in Electronics</i> , 2015 , 26, 331-335 | 2.1 | 3 |
|-----|--|--------------------|----|
| 123 | Silicon heterojunction solar cells with novel fluorinated n-type nanocrystalline silicon oxide emitters on p-type crystalline silicon. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KD03 | 1.4 | 2 |
| 122 | The influence of hydrogen gas in the ambient gas mixture on the properties of indium tin oxide films deposited on glass and acrylic substrates by dc magnetron sputtering. <i>Journal Physics D: Applied Physics</i> , 2006 , 39, 3838-3843 | 3 | 4 |
| 121 | Preparation and characterization of n-type microcrystalline hydrogenated silicon oxide films. Journal Physics D: Applied Physics, 2002, 35, 1205-1209 | 3 | 24 |
| 120 | Development of stabilized dual gap double junction a-Si solar cell using helium diluted a-Si: H intrinsic layer. <i>Journal Physics D: Applied Physics</i> , 2002 , 35, 3060-3064 | 3 | 2 |
| 119 | Role of hydrogen in controlling the growth of E-Si:H films from argon diluted SiH4 plasma. <i>Journal of Applied Physics</i> , 2002 , 91, 5442-5448 | 2.5 | 37 |
| 118 | Development of High Quality P-Type Hydrogenated Amorphous Silicon Oxide Film and Its Use in Improving the Performance of Single Junction Amorphous Silicon Solar Cells. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, 765-769 | 1.4 | 19 |
| 117 | The Growth of Crystallinity in Undoped SiO:H Films at Low RF-Power Density and Substrate Temperature. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, L94-L96 | 1.4 | 6 |
| 116 | Heterogeneity in microcrystalline-transition state: Origin of Si-nucleation and microcrystallization at higher rf power from Ar-diluted SiH4 plasma. <i>Journal of Applied Physics</i> , 2001 , 89, 3041-3048 | 2.5 | 42 |
| 115 | Control of Crystallization at Low Thickness in pc-Si:H Films Using Layer-by-Layer Growth Scheme. Japanese Journal of Applied Physics, 1999 , 38, L1087-L1090 | 1.4 | 22 |
| 114 | The role of ZnO:Al films in the performance of amorphous-silicon based tandem solar cells. <i>Journal Physics D: Applied Physics</i> , 1999 , 32, 213-218 | 3 | 24 |
| 113 | Improvement in the optoelectronic properties of a-SiO:H films. <i>Journal of Materials Science</i> , 1999 , 34, 1051-1054 | 4.3 | 12 |
| 112 | Intrinsic Hydrogenated Microcrystalline Silicon Oxide Films Prepared by RF Glow Discharge. <i>Journal of Materials Science Letters</i> , 1998 , 17, 2097-2100 | | 9 |
| 111 | Textured aluminium-doped ZnO thin films prepared by magnetron sputtering. <i>Journal Physics D: Applied Physics</i> , 1996 , 29, 1873-1877 | 3 | 18 |
| 110 | Study of effects of interelectrode spacing and preheating of source gases on hydrogenated amorphous silicon films prepared at high growth rates. <i>Journal of Applied Physics</i> , 1995 , 78, 3193-3199 | 2.5 | 5 |
| 109 | Efficient Boron Incorporation in Hydrogenated Amorphous Silicon Films by a Novel Combination of RF Glow Discharge Technique and Heated Filament. <i>Japanese Journal of Applied Physics</i> , 1995 , 34, 5743- | - 57 50 | 7 |
| 108 | Role of boron in the structural and electronic properties of hydrogenated silicon films deposited by r.f. magnetron sputtering. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1995 , 71, 115-125 | | 1 |
| 107 | The role of hydrogen dilution and radio frequency power in the formation of microcrystallinity of n-type Si:H thin film. <i>Journal of Applied Physics</i> , 1993 , 74, 5561-5568 | 2.5 | 29 |

| 106 | Diamond-Like Carbon Films Prepared by Photochemical Vapour Deposition. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, L1559-L1561 | 1.4 | 10 |
|-----|--|-----|----|
| 105 | Hydrogen plasma degradation of SnO2:F films prepared by the APCVD method. <i>Journal Physics D: Applied Physics</i> , 1993 , 26, 2144-2147 | 3 | 7 |
| 104 | Control of powder formation in silane discharge by cathode heating and hydrogen dilution for high-rate deposition of hydrogenated amorphous silicon thin films. <i>Journal of Applied Physics</i> , 1993 , 74, 4540-4545 | 2.5 | 10 |
| 103 | Hydrogenated amorphous silicon films prepared at high substrate temperature: Properties and light induced degradation. <i>Journal of Applied Physics</i> , 1993 , 73, 7435-7440 | 2.5 | 7 |
| 102 | Effect of hydrogen flow rate on the properties of magnetron sputtered hydrogenated microcrystalline silicon. <i>Journal of Materials Science Letters</i> , 1993 , 12, 1316-1319 | | 2 |
| 101 | Role of hydrogen dilution and diborane doping on the growth mechanism of p-type microcrystalline silicon films prepared by photochemical vapor deposition. <i>Journal of Applied Physics</i> , 1992 , 71, 5205-5211 | 2.5 | 32 |
| 100 | Formation of microcrystallinity in hydrogenated silicon films deposited with a simple modification of the magnetron sputtering method. <i>Journal of Materials Science Letters</i> , 1991 , 10, 1468-1470 | | 3 |
| 99 | Study of hydrogenated amorphous silicon nitride films prepared by RF magnetron sputtering. <i>Applied Physics A: Solids and Surfaces</i> , 1991 , 52, 339-343 | | 2 |
| 98 | Laser-induced structural changes in magnetron-sputtered hydrogenated microcrystalline silicon films. <i>Physical Review B</i> , 1991 , 43, 4503-4506 | 3.3 | 7 |
| 97 | Polycrystalline silicon carbide films deposited by low-power radio-frequency plasma decomposition of SiF4-CF4-H2 gas mixtures. <i>Journal of Applied Physics</i> , 1991 , 69, 3915-3923 | 2.5 | 25 |
| 96 | Influence of Chamber Pressure on Hydrogen Bonding Configurations in a-SiGe:H Films Prepared by Photo-CVD. <i>Japanese Journal of Applied Physics</i> , 1990 , 29, 2365-2370 | 1.4 | 3 |
| 95 | Radiofrequency-plasma-deposited hydrogenated fluorinated silicon-carbon alloy films. <i>Physical Review B</i> , 1989 , 40, 3830-3836 | 3.3 | 10 |
| 94 | Comparison of the properties of hydrogenated microcrystalline silicon films deposited by photothemical-vapor deposition and glow-discharge deposition processes. <i>Journal of Applied Physics</i> , 1989 , 66, 4709-4714 | 2.5 | 11 |
| 93 | Low-power deposition of fluorinated microcrystalline silicon hydrogen alloy films. <i>Journal of Applied Physics</i> , 1989 , 65, 4024-4027 | 2.5 | 8 |
| 92 | Effect of ultraviolet irradiation on the white light degraded electronic properties of hydrogenated amorphous silicon films. <i>Applied Physics Letters</i> , 1989 , 55, 1975-1977 | 3.4 | 7 |
| 91 | Phosphorus Doping and Photoinduced Changes in Hydrogenated Amorphous Silicon-Carbon Alloy Films. <i>Japanese Journal of Applied Physics</i> , 1989 , 28, 1776-1779 | 1.4 | 7 |
| 90 | Microcrystalline Silicon Films Produced by RF Magnetron Sputtering and the Effect of Diffrent Ambients on their Conductivity. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 164, 69 | | 1 |
| 89 | A Simple Modification of the Magnetron Sputtering Method for Deposition of Hydrogenated Amorphous Silicon Films with Improved Optoelectronic Properties. <i>Japanese Journal of Applied</i> | 1.4 | 2 |

(1978-1987)

| 88 | Degradation of tin-doped indium-oxide film in hydrogen and argon plasma. <i>Journal of Applied Physics</i> , 1987 , 62, 912-916 | 2.5 | 87 |
|----|---|------|-----|
| 87 | Influence of deposition parameters on the properties of boron-doped amorphous silicon-carbide films. <i>Journal of Applied Physics</i> , 1987 , 62, 3917-3921 | 2.5 | 9 |
| 86 | Thickness dependence of the properties of magnetron sputtered indium tin oxide films. <i>Journal of Materials Science Letters</i> , 1987 , 6, 1203-1204 | | 7 |
| 85 | Photo-induced changes in the properties of undoped and boron-doped a-Si:H films. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1986 , 54, 301-309 | | 19 |
| 84 | Structural characterization of tin doped indium oxide films prepared by magnetron sputtering. <i>Journal of Materials Science</i> , 1985 , 20, 2937-2944 | 4.3 | 9 |
| 83 | Photodissociation of HeH+molecular ion. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1984 , 17, 1537-1545 | | 8 |
| 82 | Properties of tin doped indium oxide thin films prepared by magnetron sputtering. <i>Journal of Applied Physics</i> , 1983 , 54, 3497-3501 | 2.5 | 266 |
| 81 | Photodissociation of MgH in the solar atmosphere. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1983 , 16, 2377-2384 | | 3 |
| 80 | Properties of Tellurium Doped Vacuum Evaporated CdS Thin Films. <i>Japanese Journal of Applied Physics</i> , 1982 , 21, L43-L45 | 1.4 | 2 |
| 79 | Transport properties of lithium and sodium doped nickel oxide. <i>Physica Status Solidi A</i> , 1981 , 65, 365-37 | 0 | 25 |
| 78 | Rotational cross sections and rate coefficients fore-CO ande-HCN collisions under interstellar conditions. <i>Physical Review A</i> , 1981 , 23, 2926-2932 | 2.6 | 9 |
| 77 | Properties of Vacuum-Evaporated CdS Thin Films. <i>Japanese Journal of Applied Physics</i> , 1980 , 19, 1889-18 | 89.5 | 39 |
| 76 | Photodissociation of H2+by the 1sg-maputransition. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1980 , 13, 3755-3762 | | 8 |
| 75 | The diffusion of nickel into copper and copperflickel alloys. <i>Physica Status Solidi A</i> , 1979 , 56, 149-155 | | 15 |
| 74 | The effect of a magnetic field on the thermal conductivity of NO№2 and NO№2 mixtures. <i>Journal of Chemical Physics</i> , 1979 , 71, 1414-1417 | 3.9 | 1 |
| 73 | Total Cross Sections of Na Scattered by Different Gases. <i>Journal of the Physical Society of Japan</i> , 1979 , 46, 205-207 | 1.5 | |
| 72 | Photodissociation of HeH2+and flux deficiency of stellar spectra. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1979 , 12, 3553-3561 | | 5 |
| 71 | The diffusion of iron in copper and of nickel in silver. <i>Physica Status Solidi A</i> , 1978 , 45, 657-663 | | 23 |

| 70 | Photodissociation of HeH+by both electronic and vibrational transitions. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1978 , 11, 3349-3356 | | 13 |
|----|---|-----|----|
| 69 | Rotational transitions of HD+in collisions with He. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1978 , 11, 1953-1963 | | 1 |
| 68 | Small-angle scattering in atom-molecule collisions: an interpretation of experimental results for the Ar-TlF system. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1978 , 11, 1965-1973 | | 1 |
| 67 | The effect of magnetic field on the heat conductivity of O2N2 and O2H2 gas mixtures. <i>Journal of Chemical Physics</i> , 1978 , 68, 3226-3230 | 3.9 | 3 |
| 66 | Rotational transitions in collisions between polar molecules: an application of the semiclassical strong-coupling method to HCl-HCl collisions. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1977 , 10, 1557-1572 | | 7 |
| 65 | Rotational transitions in collisions between molecular ions: First-order calculations for HD+-HD+. <i>Physical Review A</i> , 1977 , 16, 144-149 | 2.6 | 1 |
| 64 | Molecular Beam Studies of Total Cross Sections of Na Scattered by Different Gases. <i>Journal of the Physical Society of Japan</i> , 1977 , 42, 616-620 | 1.5 | 2 |
| 63 | The effect of nonspherical interactions on the collision integrals for He⊞2, He⊞D, and He⊞T systems. <i>Journal of Chemical Physics</i> , 1976 , 64, 5312-5313 | 3.9 | 1 |
| 62 | Thermal diffusion in binary mixtures of linear molecules. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1976 , 9, 1975-1987 | | 2 |
| 61 | The effect of non-spherical potential terms on the interaction second virial coefficient for the systems He-H2, He-HD and He-HT. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1976 , 9, 2723-273 | 0 | 1 |
| 60 | The electrical resistivity and temperature coefficient of resistivity of cobalt films. <i>Journal Physics D: Applied Physics</i> , 1976 , 9, 2261-2267 | 3 | 16 |
| 59 | Semiclassical strong-coupling calculations for rotational excitation of HCN by collision with H2. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1976 , 9, 2341-2353 | | 2 |
| 58 | Impurity diffusion in metals. Tin in copper and lead in silver. <i>Physica Status Solidi A</i> , 1975 , 32, 345-350 | | 13 |
| 57 | Effects of agglomeration and magnetic boundary scattering on the electrical resistivity of nickel films. <i>Journal of Applied Physics</i> , 1975 , 46, 3465-3467 | 2.5 | 5 |
| 56 | Dissociation of H2+ ion by collision-induced vibrational excitation. <i>Journal of Chemical Physics</i> , 1975 , 62, 4373-4379 | 3.9 | 11 |
| 55 | Vibrational-rotational excitations of the (HeH)+ ion by collisions with positrons. <i>Physical Review A</i> , 1975 , 12, 796-800 | 2.6 | 2 |
| 54 | Rotational excitation of HD+by electron and positron impact. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1975 , 8, 2283-2292 | | 5 |
| 53 | Studies on the Thermal Diffusion in the Binary Gas Mixtures Ne-N2O and Kr-N2O. <i>Journal of the Physical Society of Japan</i> , 1974 , 37, 1089-1097 | 1.5 | 2 |

| 52 | Thermal diffusion in polyatomic gas mixtures: methane-nitrogen and methane-carbon dioxide systems. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1974 , 7, 178-184 | | 7 | |
|----|---|-----------------|----|--|
| 51 | Semiclassical close-coupling calculations for rotational transitions in polar diatom-atom collisions. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1974 , 7, 2264-2276 | | 12 | |
| 50 | Dissociation of the (HeH)+molecular ion using elliptic-type orbitals. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1974 , 7, 288-296 | | 3 | |
| 49 | Effect of short range interactions on rotational transitions of CO and NO molecules by low energy electron collisions. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1974 , 7, 973-979 | | 3 | |
| 48 | Rainbow structure for the Kihara core potential by using the uniform approximation. <i>Zeitschrift Fill Physik A</i> , 1973 , 261, 273-282 | | | |
| 47 | On the dielectric second virial coefficient of polar gases. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1973 , 6, 1327-1332 | | 3 | |
| 46 | Rotational inelasticity in polar diatom-atom scattering: application of the semi-classical time-dependent perturbation theory to the Ne-CO and Ne-HCl systems. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1973 , 6, 1824-1835 | | 7 | |
| 45 | Viscosity of the binary gas mixtures argon-methane and argon-ammonia. <i>Journal of Chemical Physics</i> , 1973 , 59, 3633-3638 | .9 | 13 | |
| 44 | Thermal Diffusion in Non-Polar-Polar System: Ne-CH3Cl and Ar-CH3Cl. <i>Journal of the Physical Society of Japan</i> , 1973 , 34, 1351-1355 | .5 | 3 | |
| 43 | Contributions of nonspherical and nonadditive molecular interactions to the third virial coefficient of a diatomic and polyatomic gas. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1972 , 5, 1676-1680 | | 1 | |
| 42 | Distortion polarization of orbitals and the asymmetry in the forward-backward scattering fragments from dissociation of (HeH)+ion. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1972 , 5, 1381-1385 | | 2 | |
| 41 | Contributions of the non-spherical interactions to the third virial coefficient of a polyatomic gas. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1972 , 5, 16-26 | | 2 | |
| 40 | Transport properties and second virial coefficient of nonpolar-polar gas mixtures. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1972 , 5, 1950-1958 | | 2 | |
| 39 | Effect of dipole moment on the collision induced dissociation of HD+ion by electron impact. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1972 , 5, 1369-1380 | | 4 | |
| 38 | On the Inversion from the Energy Dependence of Total Cross-Sections. <i>Journal of the Physical Society of Japan</i> , 1972 , 33, 468-472 | .5 | | |
| 37 | Total Cross-Sections for Dipole-Dipole Scattering by Using Effectively Spherically Symmetric Potentials. <i>Journal of the Physical Society of Japan</i> , 1971 , 30, 1158-1165 | .5 | 2 | |
| 36 | Thermal Diffusion in the System Argon-Methane. <i>Journal of the Physical Society of Japan</i> , 1971 , 31, 250-2£ | 5 \$ | 5 | |
| 35 | Angular Distribution of H+ or D+ from the Electron Impact Dissociation of HD+ Ion. <i>Journal of the Physical Society of Japan</i> , 1971 , 31, 230-235 | .5 | 3 | |

| 34 | Heat conductivity of the nonpolar-polar gas mixtures Ar-CH3Cl and Xe-CH3Cl. <i>Journal of Physics A: General Physics</i> , 1971 , 4, 944-951 | | 1 |
|----|--|-------|----|
| 33 | On the asymmetry in the angular distribution of the fragments produced from the collision induced dissociation of HD+ion. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1971 , 4, 1450-1457 | | 7 |
| 32 | Thermal diffusion in polyatomic gas mixtures: methane+methyl chloride system. <i>Transactions of the Faraday Society</i> , 1970 , 66, 1604 | | 8 |
| 31 | Dipole-dipole interaction and viscosity of polar gases. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1970 , 3, 526-535 | | 14 |
| 30 | Thermal diffusion in polyatomic gas mixtures. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1970 , 3, 1052-1061 | | 3 |
| 29 | Relaxation effects and the thermal conductivity of polyatomic gases and gas mixtures. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1970 , 3, 619-635 | | 5 |
| 28 | Composition dependence of the thermal diffusion factor for the system CO-CH3Cl and CO2-CH3Cl. <i>Journal of Physics B: Atomic and Molecular Physics</i> , 1969 , 2, 715-718 | | 2 |
| 27 | Thermal Diffusion in the Nonpolar Polar System Helium Methyl Chloride. <i>Journal of Chemical Physics</i> , 1969 , 50, 2052-2056 | 3.9 | 4 |
| 26 | Thermal Diffusion in Argontarbon Dioxide Gas Mixture. <i>Journal of Chemical Physics</i> , 1968 , 48, 5238-524 | 413.9 | 14 |
| 25 | Composition Dependence of the Thermal-Diffusion Factor in the HydrogenHelium Gas Mixture. <i>Journal of Chemical Physics</i> , 1968 , 48, 2802-2805 | 3.9 | 12 |
| 24 | Thermal Conductivity and Rotational Relaxation in Some Polar Gases. <i>Journal of Chemical Physics</i> , 1968 , 49, 2422-2425 | 3.9 | 14 |
| 23 | Thermal diffusion in the ternary system helium + neon + carbon dioxide. <i>Transactions of the Faraday Society</i> , 1968 , 64, 358 | | 3 |
| 22 | Intermolecular potentials and viscosities of some polar organic vapours. <i>Journal Physics D: Applied Physics</i> , 1968 , 1, 71-76 | 3 | 5 |
| 21 | Effect of chemical reaction on diffusion in the system N2O4 leftrightharpoons 2NO2. <i>Journal of Physics A</i> , 1968 , 1, 269-271 | | |
| 20 | Thermal Conductivity of Argon-Carbondioxide and Nitrogen-Carbondioxide Gas Mixtures. <i>Journal of the Physical Society of Japan</i> , 1968 , 25, 862-867 | 1.5 | 11 |
| 19 | On the representation of the interaction energy between two polar molecules. <i>Flow, Turbulence and Combustion</i> , 1968 , 18, 43-49 | | 2 |
| 18 | Formation of Dimers in Polar Gases: Contribution of Metastably Bound Molecules to the Second Virial Coefficient. <i>Journal of the Physical Society of Japan</i> , 1967 , 22, 77-81 | 1.5 | 4 |
| 17 | Thermal conductivities of nitrogen-argon and oxygen-argon gas mixtures. <i>British Journal of Applied Physics</i> , 1967 , 18, 1307-1310 | | 14 |

LIST OF PUBLICATIONS

| 16 | Heat conductivity and relaxation effects in the system N2O4[A: r harp over l] 2NO2. <i>Proceedings of the Physical Society</i> , 1967 , 92, 800-804 | | 2 |
|----|--|------|----|
| 15 | Thermal conductivity of some quadrupolar gases. <i>Transactions of the Faraday Society</i> , 1967 , 63, 2379 | | 13 |
| 14 | Thermal Diffusion in HydrogenHelium Gas Mixture. <i>Journal of Chemical Physics</i> , 1967 , 47, 452-453 | 3.9 | 15 |
| 13 | Improved Design for the Trennschaukel: Measurement of the Thermal-Diffusion Factors in Gas Mixtures. <i>Journal of Chemical Physics</i> , 1967 , 47, 448-451 | 3.9 | 11 |
| 12 | Thermal conductivity of hydrogen-nitrogen and hydrogen-carbon-dioxide gas mixtures. <i>British Journal of Applied Physics</i> , 1967 , 18, 1301-1306 | | 13 |
| 11 | Viscosity and intermolecular potentials of hydrogen sulphide, sulphur dioxide and ammonia. <i>Transactions of the Faraday Society</i> , 1967 , 63, 341 | | 28 |
| 10 | Thermal conductivity of hydrogen-helium gas mixtures. British Journal of Applied Physics, 1967, 18, 635 | -640 | 31 |
| 9 | Chemical reaction and diffusion coefficients in the heat conductivity of chemically reacting gas mixtures. <i>Transactions of the Faraday Society</i> , 1966 , 62, 3131 | | 3 |
| 8 | The influence of bound molecules on the thermal conductivity in the critical region. <i>Flow, Turbulence and Combustion</i> , 1965 , 15, 313-321 | | 1 |
| 7 | Force Constants of N2O4 and NO2 and the Viscosity of the Dissociating System N2O4?2NO2. <i>Journal of Chemical Physics</i> , 1965 , 43, 4140-4142 | 3.9 | 9 |
| 6 | Viscosity of Hydrogen, Deuterium, Methane, and Carbon Monoxide from B 011 to 15011C below 200 Atmospheres. <i>Journal of Chemical Physics</i> , 1964 , 41, 374-378 | 3.9 | 56 |
| 5 | Thermal conductivity of slowly reacting systems. <i>Transactions of the Faraday Society</i> , 1963 , 59, 2522 | | 3 |
| 4 | Thermal Conductivity and Equilibrium Constant of the System N2O4?2NO2. <i>Journal of Chemical Physics</i> , 1961 , 35, 329-334 | 3.9 | 20 |
| 3 | Effect of Relaxation of Chemical Energy on the Thermal Conductivity of the System N2O4?2NO2. Journal of Chemical Physics, 1961 , 35, 649-651 | 3.9 | 3 |
| 2 | Rotational-Translational Relaxation Time in H2Calculated from Thermal Conductivity. <i>Proceedings of the Physical Society</i> , 1961 , 77, 677-681 | | 2 |
| 1 | Thermal Conductivity of Binary Mixtures of Diatomic and Monatomic Gases. <i>Journal of Chemical Physics</i> , 1960 , 32, 427-435 | 3.9 | 35 |